

General description

Femtofarad bidirectional ElectroStatic Discharge (ESD)protection diode in a leadless ultra small DFN1006 Surface-Mounted Device(SMD)plastic package designed to protect one signal line from the damage caused by ESD and other transients.The combination of extremely low capacitance, high ESD maximum rating and ultra small package makes the device ideal for high-speed data line protection and antenna protection applications.

Features and benefits

- Bidirectional ESD protection of one line
- Femtofarad capacitance: $C_i = 0.55\text{pF}$ (Typ)
- Low clamping voltage $V_c = 15\text{ V@3A}$
- Ultra Low Leakage:nA Level
- Response time is typically<1 ns
- IEC 61000-4-2;level 4 (ESD)

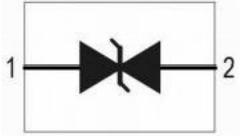
Application information

- | | |
|---|----------------------------|
| ·10/100/1000 Mbit/s Ethernet | ·Portable electronics |
| ·FireWire | ·Communication systems |
| ·High-speed data lines | ·Computers and peripherals |
| ·Subscriber Identity Module (SIM) card protection | ·Audio and video equipment |
| ·Cellular handsets and accessories | ·Antenna protection |

Ordering information

| Device | Package | Marking | Packaging |
|-----------|------------|---------|------------------|
| ESD8L5.0C | DFN1006-2L | N | 10000/Tape &Reel |

Schematic &Pin configuration

| Simplified outline | | | Graphic symbol |
|--------------------|---|--|---|
| | | | |
| 1 | 2 | |  |

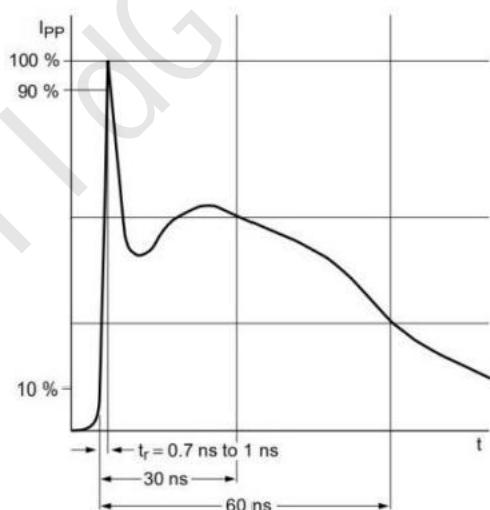
Maximum Ratings (Top=25°C,unless otherwise specified)

| | Parameter | Symbol | Value | Unit |
|---|-----------|-------------|-------|------|
| Peak Pulse Power (Tp =8/20 μ s) | PppM | 45 | W | |
| Rated Peak Pulse Current (Tp=8/20 μ s) | IppM | 3 | A | |
| Maximum lead temperature for soldering during 10s | TL | 260 | ° C | |
| Storage Temperature Range | Tstg | -55 to +150 | ° C | |
| Operating Temperature Range | Top | -40 to +125 | ° C | |
| Maximum junction temperature | Tj | 150 | ° C | |
| ESD voltage IEC 61000-4-2 (air discharge) | VESD | 15 | kV | |
| ESD voltage IEC 61000-4-2 (contact discharge) | VESD | 8 | kV | |

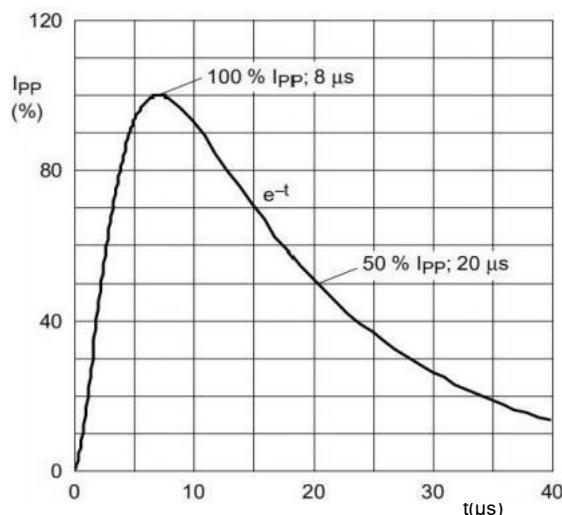
Electrical Characteristics (Top=25C,unless otherwise specified)

| | Parameter | Symbol | Min | Typ | Max | Unit | Condition |
|-------------------------|-----------|--------|------|-----|------|------|--------------------|
| Reverse Working Voltage | VRWM | | | | 5.0 | V | |
| Breakdown Voltage | VBR | 6.5 | | | 9.0 | V | Ir=1mA |
| Leakage Current ILeak | IR | | | | 100 | nA | VRwM=5V |
| Clamping Voltage | Vc | | | | 15.0 | V | pp=3A, Tp=8/20 μ s |
| Junction Capacitance | Cj | | 0.55 | 0.8 | | pF | Vr=0V, f=1MHz |

Typical Electrical and Thermal Characteristics (Curves)



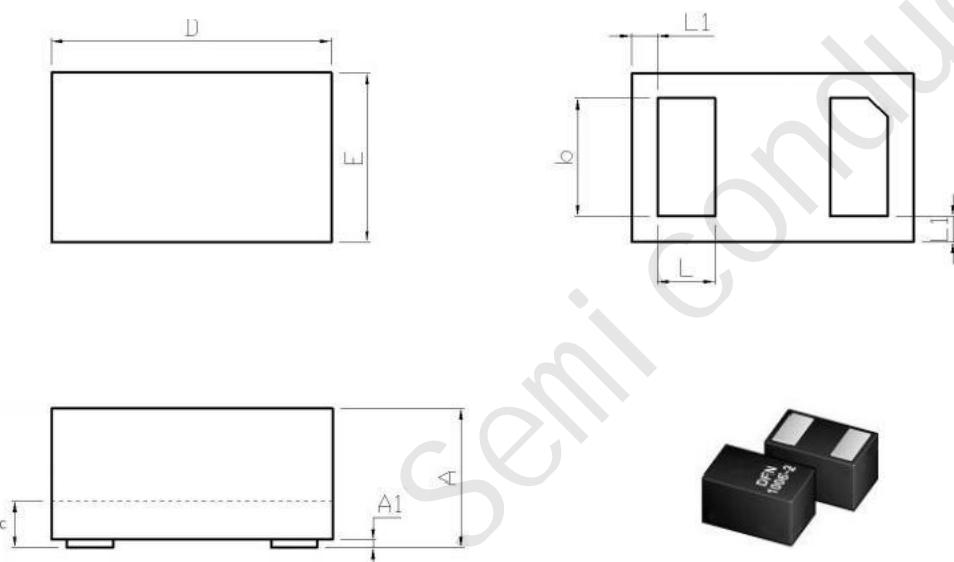
IEC61000-4-2 Waveform



IEC 61000-4-5 Waveform(8/20μs pulse)

Package Outline Dimensions

DFN1006-2L



DFN1006-2L (mm)

| Dim | Min | Typ. | Max |
|-----|-------|------|-------|
| A | 0.46 | 0.48 | 0.50 |
| A1 | 0 | 0.02 | 0.05 |
| b | 0.45 | 0.5 | 0.55 |
| C | 0.1 | 0.12 | 0.14 |
| D | 0.95 | 1.00 | 1.05 |
| E | 0.55 | 0.60 | 0.65 |
| L | 0.20 | 0.25 | 0.30 |
| L1 | 0.035 | 0.05 | 0.065 |
| h | 0.07 | 0.12 | 0.17 |